# ne<mark>x</mark>peria

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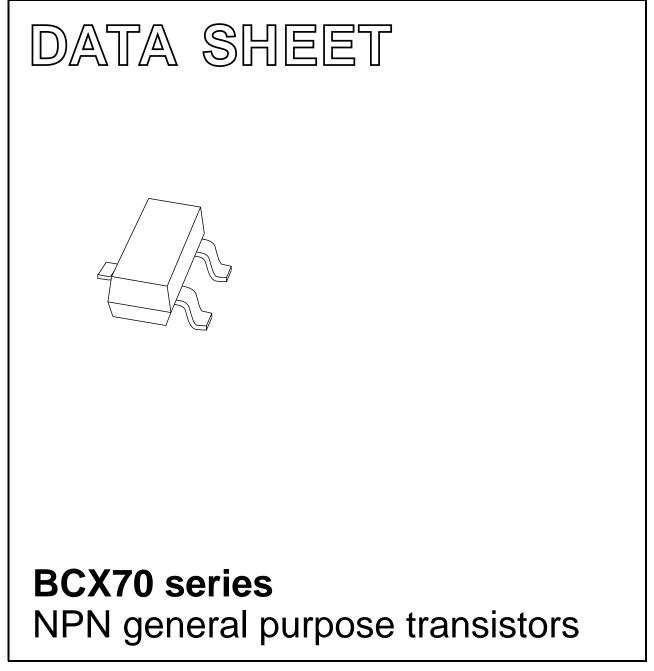
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If you have any questions related to the data sheet, please contact our nearest sales office via e-mail or telephone (details via **salesaddresses@nexperia.com**). Thank you for your cooperation and understanding,

Kind regards,

Team Nexperia

## DISCRETE SEMICONDUCTORS



Product data sheet Supersedes data of 1999 Apr 15 2004 Jan 16



### FEATURES

- Low current (max. 100 mA)
- Low voltage (max. 45 V).

### APPLICATIONS

• General purpose switching and amplification.

### DESCRIPTION

NPN transistor in a SOT23 plastic package. PNP complements: BCX71 series.

#### MARKING

TYPE NUMBER	MARKING CODE <sup>(1)</sup>
BCX70G	AG*
BCX70H	AH*
BCX70J	AJ*
BCX70K	AK*

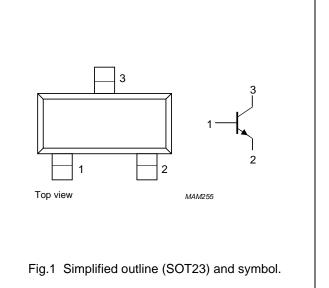
### Note

- 1. \* = p : Made in Hong Kong.
  - \* = t : Made in Malaysia.
  - \* = W : Made in China.

### ORDERING INFORMATION

### PINNING

PIN	DESCRIPTION	
1	base	
2	emitter	
3	collector	



TYPE		PACKAGE	
NUMBER NAME		DESCRIPTION	VERSION
BCX70G	—	plastic surface mounted package; 3 leads	SOT23
BCX70H			
BCX70J			
BCX70K			

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### BCX70 series

### BCX70 series

### LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>CBO</sub>	collector-base voltage	open emitter	_	45	V
V <sub>CEO</sub>	collector-emitter voltage	open base	-	45	V
V <sub>EBO</sub>	emitter-base voltage	open collector	-	5	V
I <sub>C</sub>	collector current (DC)		_	100	mA
I <sub>CM</sub>	peak collector current		-	200	mA
I <sub>BM</sub>	peak base current		-	200	mA
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$	_	250	mW
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C
T <sub>amb</sub>	operating ambient temperature		-65	+150	°C

### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT	
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	note 1	500	K/W	

### Note

1. Transistor mounted on an FR4 printed-circuit board.

### BCX70 series

### CHARACTERISTICS

 $T_{amb}$  = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I <sub>CBO</sub>	collector cut-off current	I <sub>E</sub> = 0; V <sub>CB</sub> = 45 V	-	-	20	nA
		I <sub>E</sub> = 0; V <sub>CB</sub> = 45 V; T <sub>amb</sub> = 150 °C	—	_	20	μA
I <sub>EBO</sub>	emitter cut-off current	I <sub>C</sub> = 0; V <sub>EB</sub> = 4 V	_	-	20	nA
h <sub>FE</sub>	DC current gain	$I_{C} = 10 \ \mu A; V_{CE} = 5 \ V$				
	BCX70G		_	-	-	
	BCX70H		40	-	-	
	BCX70J		30	-	-	
	BCX70K		100	_	_	
	DC current gain	I <sub>C</sub> = 2 mA; V <sub>CE</sub> = 5 V				
	BCX70G		120	-	220	
	BCX70H		180	_	310	
	BCX70J		250	_	460	
	BCX70K		380	-	630	
	DC current gain	I <sub>C</sub> = 50 mA; V <sub>CE</sub> = 1 V				
	BCX70G		50	-	-	
	BCX70H		70	-	-	
	BCX70J		90	_	_	
	BCX70K		100	-	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	I <sub>C</sub> = 10 mA; I <sub>B</sub> = 0.25 mA	50	_	350	mV
		I <sub>C</sub> = 50 mA; I <sub>B</sub> = 1.25 mA	100	-	550	mV
V <sub>BEsat</sub>	base-emitter saturation voltage	I <sub>C</sub> = 10 mA; I <sub>B</sub> = 0.25 mA	600	_	850	mV
		I <sub>C</sub> = 50 mA; I <sub>B</sub> = 1.25 mA	700	-	1050	mV
V <sub>BE</sub>	base-emitter voltage	I <sub>C</sub> = 10 μA; V <sub>CE</sub> = 5 V	—	520	_	mV
		I <sub>C</sub> = 2 mA; V <sub>CE</sub> = 5 V	550	650	750	mV
		I <sub>C</sub> = 50 mA; V <sub>CE</sub> = 1 V	_	780	-	mV
C <sub>c</sub>	collector capacitance	I <sub>E</sub> = i <sub>e</sub> = 0; V <sub>CB</sub> = 10 V; f = 1 MHz	—	1.7	_	pF
C <sub>e</sub>	emitter capacitance	$I_{C} = i_{c} = 0; V_{EB} = 0.5 V; f = 1 MHz$	_	11	-	pF
f⊤	transition frequency	$I_{C} = 10 \text{ mA}; V_{CE} = 5 \text{ V}; f = 100 \text{ MHz};$ note 1	100	250	-	MHz
F	noise figure	$I_{C} = 200 \ \mu\text{A}; V_{CE} = 5 \ \text{V}; R_{S} = 2 \ \text{k}\Omega;$ f = 1 kHz; B = 200 Hz	-	2	6	dB

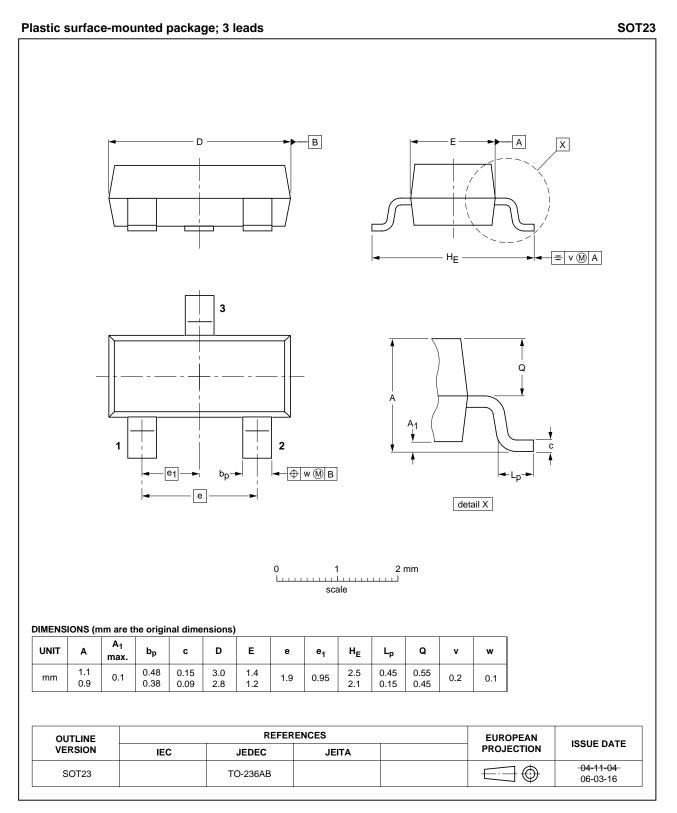
#### Note

1. Pulse test:  $t_p \leq 300~\mu s;~\delta \leq 0.02.$ 

BCX70 series

# NPN general purpose transistors

### PACKAGE OUTLINE



2004 Jan 16

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### BCX70 series

### DATA SHEET STATUS

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

#### Notes

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# **NXP Semiconductors**

### **Customer notification**

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

### **Contact information**

For additional information please visit: http://www.nxp.com For sales offices addresses send e-mail to: salesaddresses@nxp.com

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